

#### 1-Line Uni-directional TVS Diode

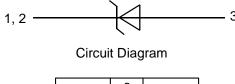
#### **Description**

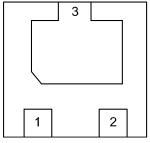
The PESDU1271P4-3 is a high power TVS, to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive lines. The PESDU1271P4-3 complies with the IEC 61000-4-2 (ESD) standard with ±30kV air and ±30kV contact discharge. It is assembled into a 3-pin DFN2020- 3 lead–free package. Each device will protect one line. The combination of small size, and high surge capability makes them ideal for use in applications such as cell phones, LCD displays, USB, and multi media card interfaces.

#### **Features**

- 7680W peak pulse power (8/20µs)
- operating voltage: 12V
- Ultra low clamping voltage
- · One power line protects
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    Air discharge: ±30kV
    Contact discharge: ±30kV
  - IEC61000-4-5 (Lightning) 240A (8/20µs)
- RoHS Compliant

### **Dimensions and Pin Configuration**





Transparent top view

#### **Mechanical Characteristics**

Package: DFN2020-3

Case Material: "Green" Molding Compound

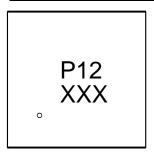
Moisture Sensitivity: Level 1 per J-STD-020

Marking Information: See Below

### **Applications**

- I/O Interfaces
- Power lines
- Automotive and Telecommunication
- Computer & Consumer Electronics
- Industrial Electronics
- Microcontroller Input Protection

### **Marking Information**



P12 XXX= Device Making Code

#### **Ordering Information**

Part Number	Shipping	Reel Size
PESDU1271P4-3	3000/Tape & Reel	7 inch



# Absolute Maximum Ratings (TA=25°C unless otherwise specified)

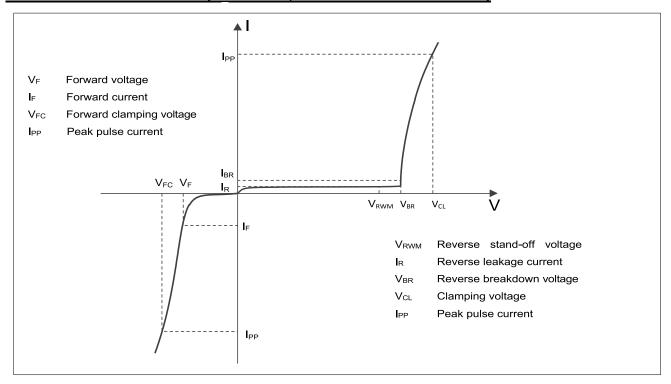
Parameter	Symbol	Value	Unit	
Peak Pulse Power (8/20µs)	P <sub>PK</sub>	7680	W	
Peak Pulse Current (8/20µs)	lpp	240	А	
ESD per IEC 61000-4-2 (Air)	Vesd	±30	kV	
ESD per IEC 61000-4-2 (Contact)	VESD	±30	N V	
Lead temperature	TL	260	°C	
Operating Temperature Range	Тор	-40 ~ +85	°C	
Storage Temperature Range	T <sub>STG</sub>	−55 ~ <b>+</b> 150	°C	

# Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	V <sub>RWM</sub>			12	V	
Breakdown Voltage	$V_{BR}$	13			V	I <sub>T</sub> = 1mA
Reverse Leakage Current	I <sub>R</sub>			1	μΑ	V <sub>RWM</sub> = 12V
Clamping Voltage	Vc			20	V	I <sub>PP</sub> = 20A (8/20μs pulse)
Clamping Voltage	Vc			32	V	I <sub>PP</sub> = 240A (8/20µs pulse)
Junction Capacitance	CJ		700		pF	V <sub>R</sub> = 0V, f = 1MHz



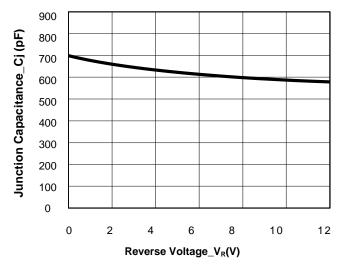
# Electrical characteristics (T<sub>A</sub> = 25°C, unless otherwise noted)



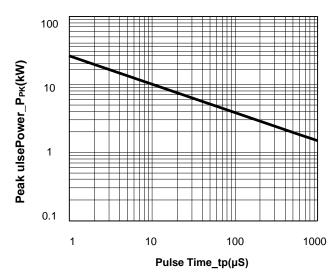
Definitions of electrical characteristics



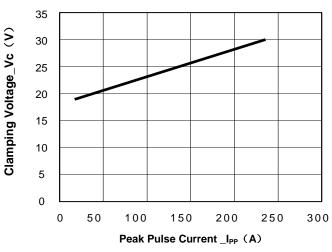
## Typical Performance Characteristics (TA=25°C unless otherwise Specified)



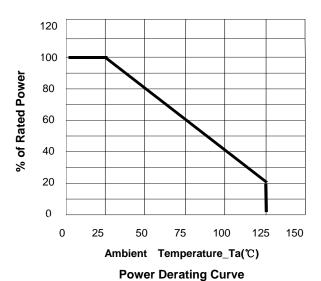
Junction Capacitance vs. Reverse Vlotage



Peak Pulse Power vs. Pulse Time



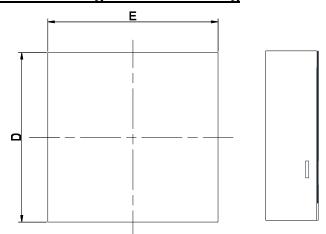
Clamping Voltage vs.Peak Pulse Current



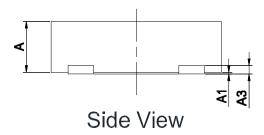
110 100 % of Peak Pulse Current 90 80 70 60 50 40 30 20 10 0 10 20 30 Time\_t(µs) 8/20µs Pulse Waveform



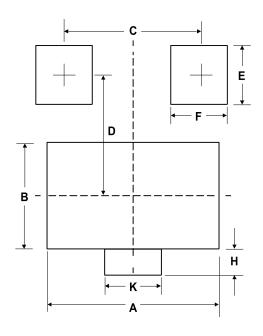
# **DFN2020-3 Package Outline Drawing**

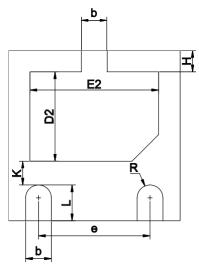


Top View



## **Suggested Land Pattern**





# **Bottom View**

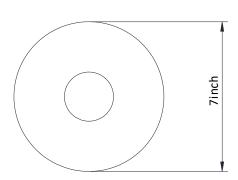
Symbol	Dimen	sions In Milli	meters
	Min.	Тур.	Max
Α	0.55	0.60	0.65
A1	0.00	0.02	0.05
А3		0.10 REF.	
b	0.25	0.30	0.35
D	1.90	2.00	2.10
Е	1.90	2.00	2.10
D2	0.95	1.05	1.15
E2	1.40	1.50	1.60
е	1.20	1.30	1.40
Н	0.20	0.25	0.30
K	0.20	0.30	0.40
L	0.35	0.40	0.45
R	0.13	-	-

SYM	MILLIMETERS
А	1.60
В	1.10
С	1.30
D	1.05
Е	0.50
F	0.40
K	0.40
Н	0.25

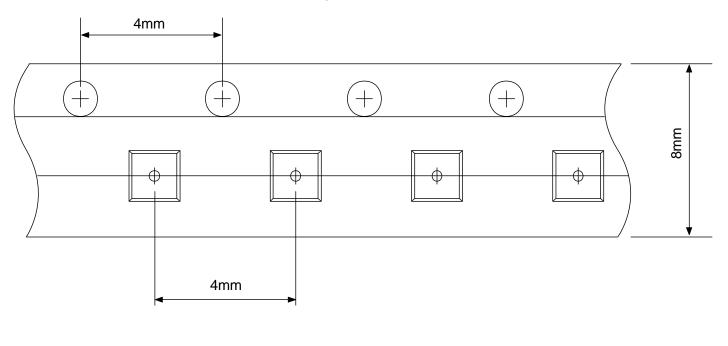


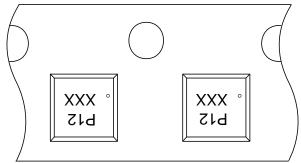
### TAPE AND REEL INFORMATION





**Tape Dimensions** 







User Direction of Feed



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